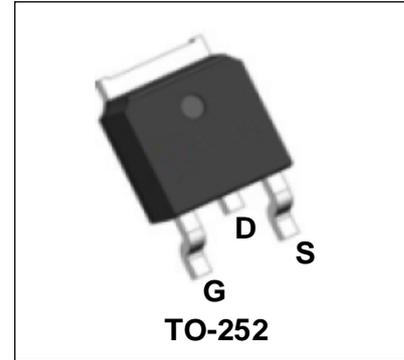


30V N-Channel Enhancement Mode Power MOSFET

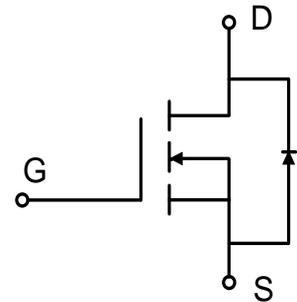
Description

WMO80N03T1 uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.



Features

- $V_{DS} = 30\text{ V}$, $I_D = 80\text{ A}$
 $R_{DS(on)} < 5.5\text{ m}\Omega @ V_{GS} = 10\text{ V}$
 $R_{DS(on)} < 9\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- Green Device Available
- Low Gate Charge
- Advanced High Cell Density Trench Technology
- 100% EAS Guaranteed



Applications

- Power Management Switches
- BMS Protection
- Synchronous Buck Converter

Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Drain-Source voltage		V_{DS}	30	V
Gate-Source voltage		V_{GS}	± 20	V
Continuous Drain Current@10V ¹	$T_C=25^\circ\text{C}$	I_D	80	A
	$T_C=100^\circ\text{C}$		57	
	$T_A=25^\circ\text{C}$		17	
	$T_A=70^\circ\text{C}$		14.5	
Pulsed Drain Current ²		I_{DM}	160	A
Single Pulse Avalanche Energy ³		EAS	115.2	mJ
Avalanche Current		I_{AS}	48	A
Total Power Dissipation ⁴	$T_C=25^\circ\text{C}$	P_D	53	W
	$T_A=25^\circ\text{C}$		2.4	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to+175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ¹	$R_{\theta JA}$	62	$^\circ\text{C/W}$
Thermal Resistance from Junction-to-Case ¹	$R_{\theta JC}$	2.8	$^\circ\text{C/W}$

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30	-	-	V	
Gate-body Leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$	$T_J = 25^\circ\text{C}$	-	-	1	μA
			$T_J = 55^\circ\text{C}$	-	-	5	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.5	2.5	V	
Drain-Source On-Resistance ²	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 30A$	-	4.7	5.5	m Ω	
		$V_{GS} = 4.5V, I_D = 15A$	-	6.0	9		
Dynamic Characteristics							
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	-	1860	-	pF	
Output Capacitance	C_{oss}		-	267	-		
Reverse Transfer Capacitance	C_{riss}		-	180	-		
Switching Characteristics							
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	-	2	-	Ω	
Total Gate Charge(4.5V)	Q_g	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 15A$	-	20	-	nC	
Gate-Source Charge	Q_{gs}		-	7.6	-		
Gate-Drain Charge	Q_{gd}		-	7.2	-		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 15V, R_G = 3.3\Omega, I_D = 15A$	-	7.8	-	nS	
Rise Time	t_r		-	15	-		
Turn-Off Delay Time	$t_{d(off)}$		-	37.3	-		
Fall Time	t_f		-	10.6	-		
Drain-source body diode Characteristics							
Diode Forward Voltage ²	V_{SD}	$I_S = 1A, V_{GS} = 0V$	-	-	1.0	V	
Continuous Source Current ^{1,5}	I_S	$V_G = V_D = 0V, \text{Force Current}$	-	-	80	A	
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 30A, di/dt = 100A/\mu s$	-	14	-	nS	
Body Diode Reverse Recovery Charge	Q_{rr}		-	5	-	nC	

Notes:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.1mH, I_{AS} = 48A$
- 4.The power dissipation is limited by 175°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

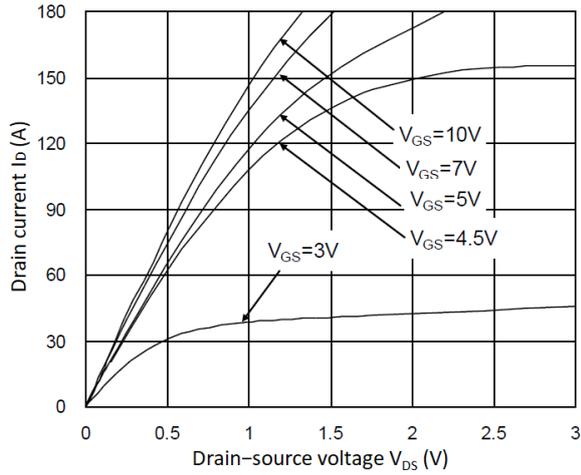


Figure 1. Output Characteristics

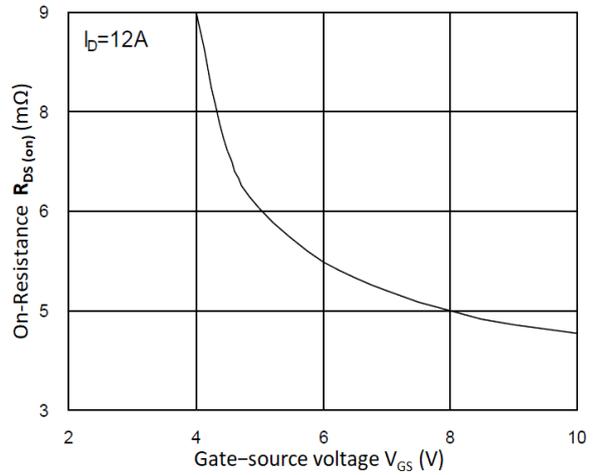


Figure 2. $R_{DS(on)}$ vs. V_{GS}

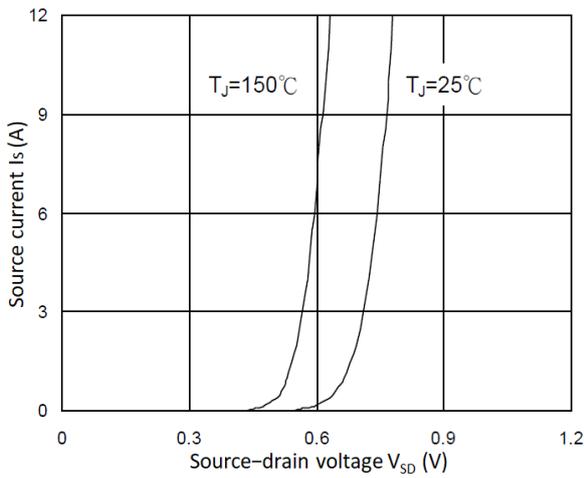


Figure 3. Forward Characteristics of Reverse

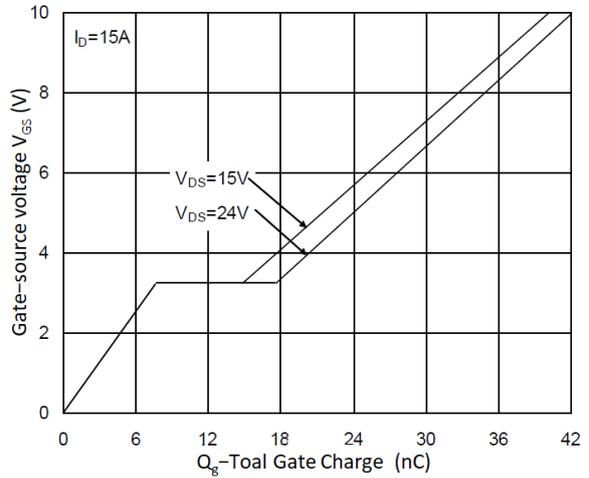


Figure 4. Gate Charge Characteristics

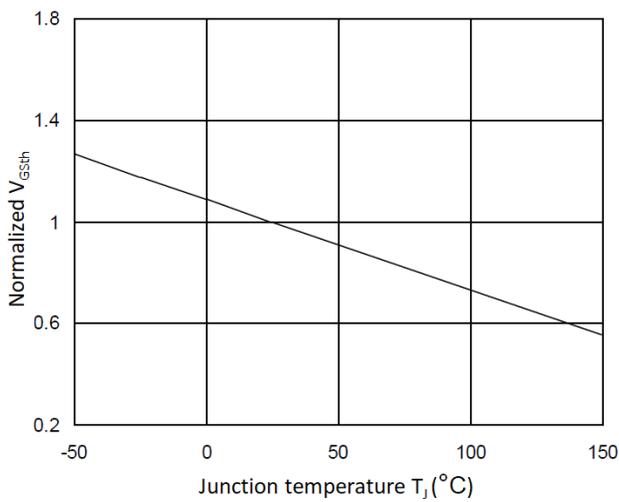


Figure 5. Normalized $V_{GS(th)}$ vs. T_J

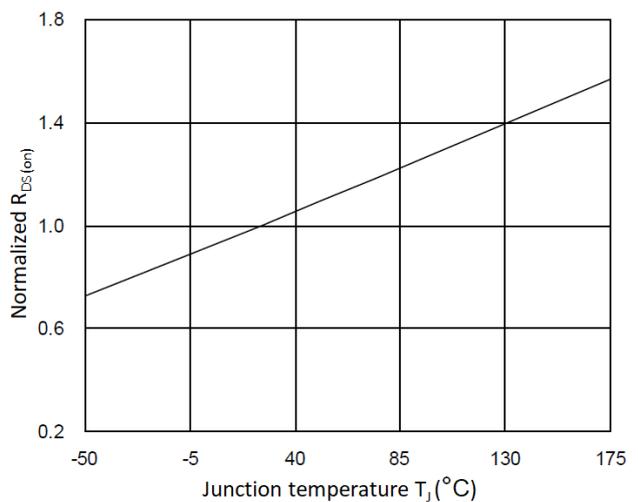


Figure 6. Normalized $R_{DS(on)}$ vs. T_J

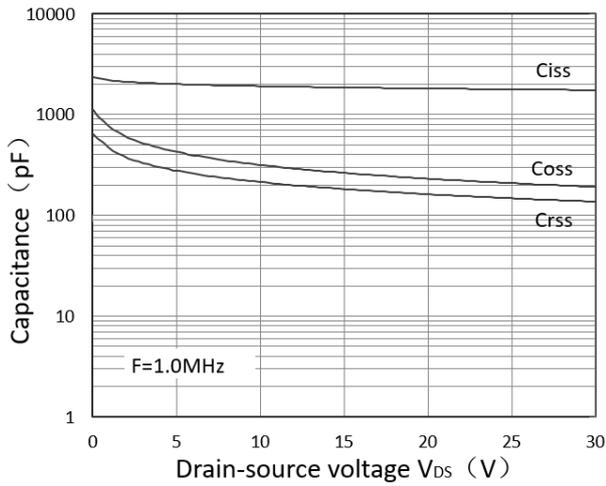


Figure 7. Capacitance Characteristics

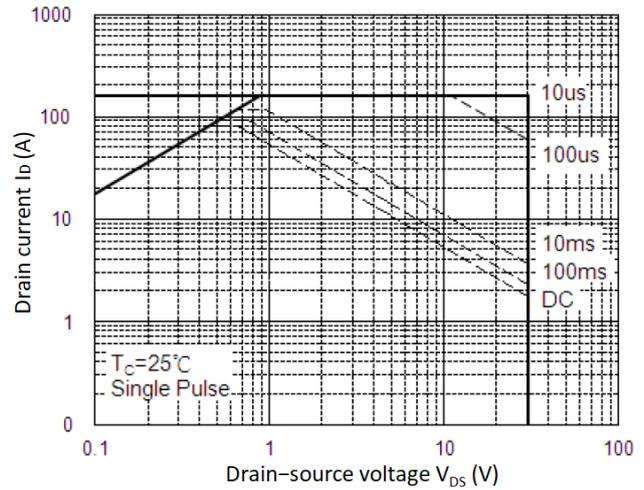


Figure 8. Safe Operating Area

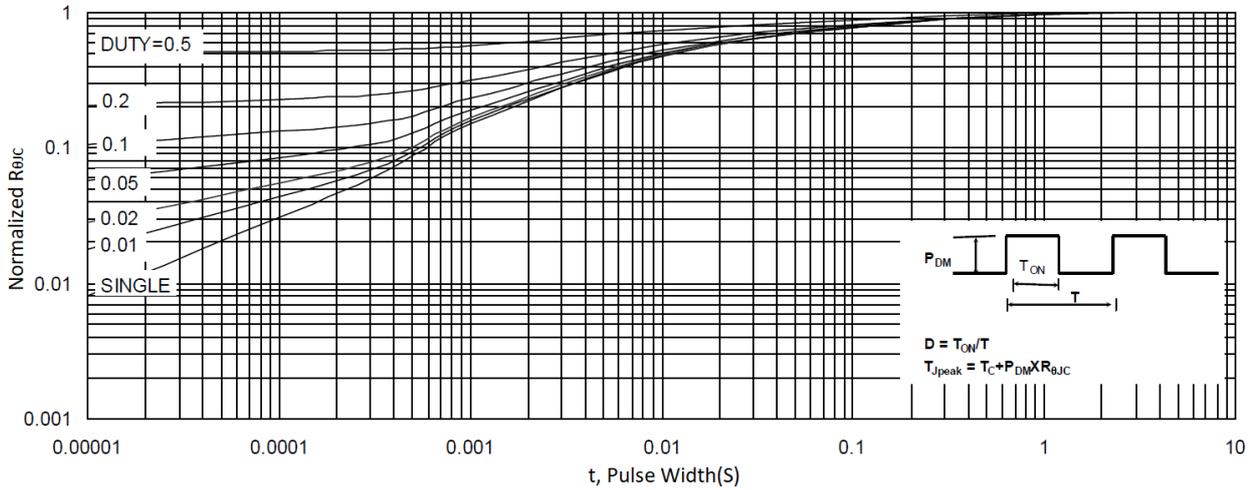


Figure 9. Normalized Maximum Transient Thermal Impedance

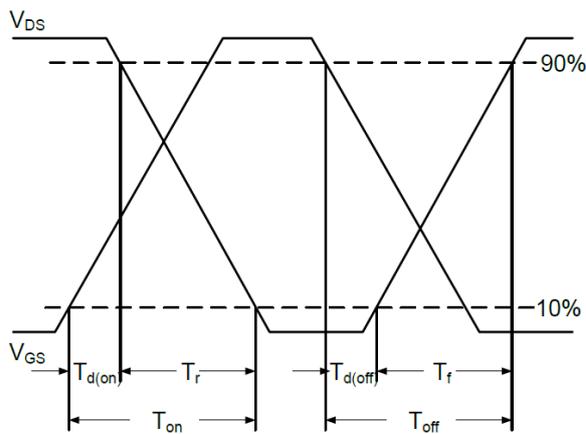


Figure 10. Switching Time Waveform

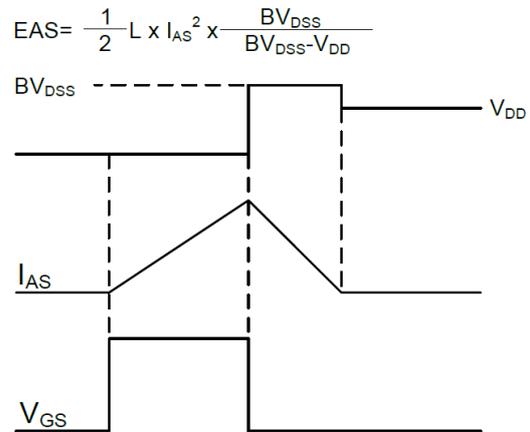
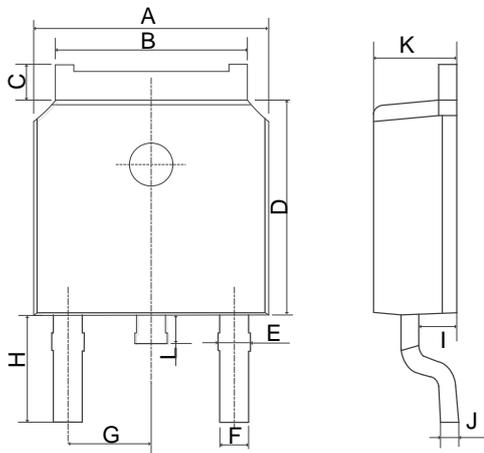


Figure 11. Unclamped Inductive Switching Waveform

Mechanical Dimensions for TO-252



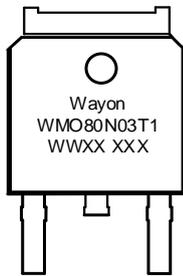
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	2.90REF	
I	0.85	1.17
J	0.51REF	
K	2.10	2.50
L	0.40	1.00

Ordering Information

Part	Package	Marking	Packing method
WMO80N03T1	TO-252	WMO80N03T1	Tape and Reel

Marking Information



WMO80N03T1 = Device code

WWXX XXX= Manufacturing code

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WAYON website: <http://www.way-on.com>

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